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Dixon  
6/25/02

<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>		Complete if Known	
		<b>Application Number</b>	
		<b>Filing Date</b>	November 2, 2001
		<b>First Named Inventor</b>	Wilfred Lerch et al
		Group Art Unit	
		Examiner Name	
		Attorney Docket No.	AZ.2964

## **U. S. PATENT DOCUMENTS**

## **FOREIGN PATENT DOCUMENTS**

**OTHER PRIOR ART & NON PATENT LITERATURE DOCUMENTS**

OTHER PRIOR ART & NON-PATENT LITERATURE DOCUMENTS		
Examiner Initials	Cite No.	
fmz	1	XP-002101565 "Rapid Thermal Process Requirements for the Annealing of Ultra-Shallow Junctions"
fmz	3	XP-000669354 "Simulation of Rapid Thermal Annealed Boron Ultra-Shallow Junctions in Inert and Oxidizing Ambient"
fmz	4	XP-000974859 "The Effects of Small Concentrations of Oxygen in RTP Annealing of Low Energy Boron, BF <sub>2</sub> and Arsenic Ion Implants"

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Examiner

James G. Maldonado

Date

11/13/2001

1/31/02